

Application No.: 10/692,838

Docket No.: JCLA7640

Amendment**In The Claims:****Claims 1-6. (Cancelled)**

Claim 7. (Currently amended) A capacitor structure corresponding to a pixel, comprising:

a bottom electrode, deposited on a substrate;

a dielectric layer, deposited on the bottom electrode;

a top electrode, corresponding to the bottom electrode and deposited on the dielectric layer, wherein the top electrode comprises a coupling part and a protruding part, the coupling part corresponds to the bottom electrode for forming a capacitor region, and the protruding part exceeds the capacitor region;

a passivation layer, covering the top electrode, wherein an opening formed in the passivation layer exposes the protruding part of the top electrode; and

a pixel electrode, covering the passivation layer and electrically connecting with the top electrode through the opening, wherein the pixel electrode is patterned to form an incision opening above the protruding part to expose the passivation layer ~~an incision opening formed in the pixel electrode on the opening and the coupling part exposes the passivation layer.~~

Claim 8. (Original) The capacitor structure of claim 7, wherein the bottom electrode is made of a metal material.

Claim 9. (Original) The capacitor structure of claim 7, wherein the top electrode is made of a metal material.

Application No.: 10/692,838

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Claim 10. (Original) The capacitor structure of claim 7, wherein the pixel electrode is made of an indium tin oxide material.

Claim 11. (Original) The capacitor structure of claim 7, wherein the dielectric layer is made of a Si_3N_4 material.